PNP Silicon General Purpose Amplifier Transistor

This PNP transistor is designed for general purpose amplifier applications. This device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

- Reduces Board Space
- High h_{FE}, 210–460 (Typical)
- Low $V_{CE(sat)}$, < 0.5 V
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Available in 4 mm, 8000 Unit Tape & Reel
- This is a Pb–Free Device

MAXIMUM RATINGS (T_A = $25^{\circ}C$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	-60	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	-50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	-6.0	Vdc
Collector Current – Continuous	lc	-100	mAdc

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	PD	265	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	-55 ~ +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

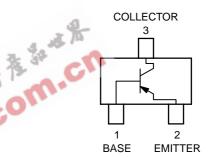
1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

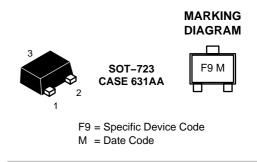


ON Semiconductor®

http://onsemi.com

PNP GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT





ORDERING INFORMATION

Device	Package	Shipping [†]
2SA2029M3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

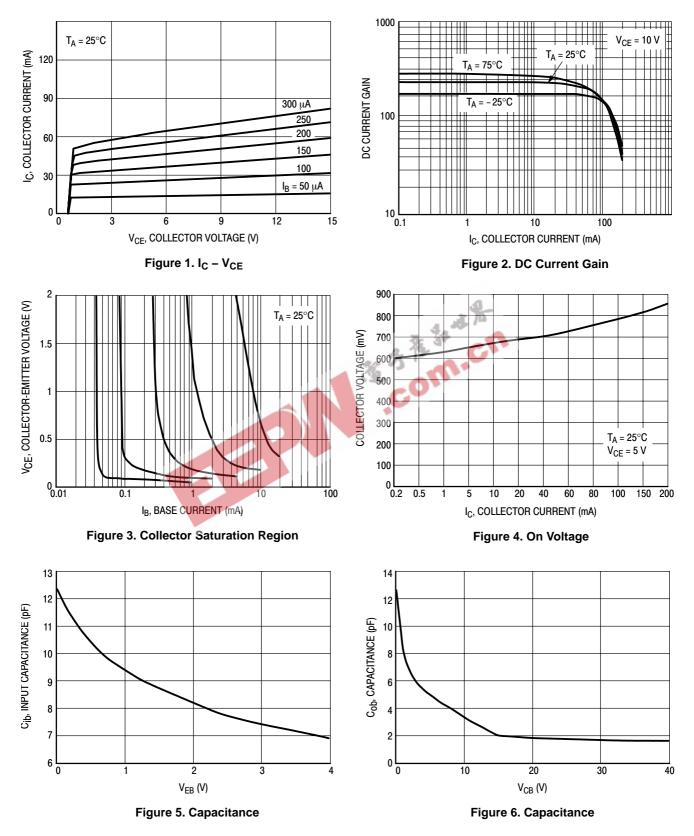
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector–Base Breakdown Voltage (I _C = $-50 \ \mu Adc$, I _E = 0)	V _{(BR)CBO}	-60	-	-	Vdc
Collector–Emitter Breakdown Voltage ($I_C = -1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	-50	-	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -50 \ \mu Adc$, $I_E = 0$)	V _{(BR)EBO}	-6.0	-	-	Vdc
Collector–Base Cutoff Current ($V_{CB} = -30$ Vdc, $I_E = 0$)	I _{CBO}	-	-	-0.5	nA
Emitter–Base Cutoff Current ($V_{EB} = -7.0 \text{ Vdc}, I_B = 0$)	I _{EBO}	-	-	-0.1	μΑ
Collector–Emitter Saturation Voltage (Note 2) ($I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)	V _{CE(sat)}	-	-	-0.5	Vdc
DC Current Gain (Note 2) ($V_{CE} = -6.0 \text{ Vdc}, I_C = -1.0 \text{ mAdc}$)	h _{FE}	120	_	560	-
Transition Frequency (V _{CE} = -12 Vdc, I _C = -2.0 mAdc, f = 30 MHz)	f _T	_	140	_	MHz
Output Capacitance ($V_{CB} = -12$ Vdc, $I_E = 0$ Adc, $f = 1.0$ MHz)	C _{OB}	-	3.5	_	pF

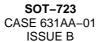
2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

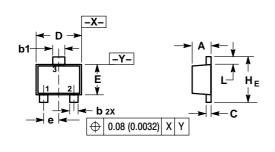


TYPICAL ELECTRICAL CHARACTERISTICS



PACKAGE DIMENSIONS

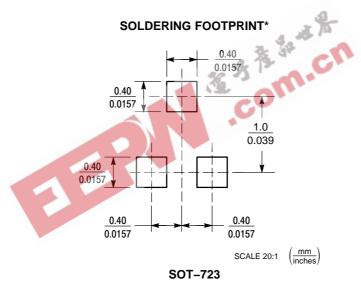




NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS.
- 2 3.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM
- THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. 4.

	МІ	LIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.45	0.50	0.55	0.018	0.020	0.022	
b	0.15	0.21	0.27	0.0059	0.0083	0.0106	
b1	0.25	0.31	0.37	0.010	0.012	0.015	
С	0.07	0.12	0.17	0.0028	0.0047	0.0067	
D	1.15	1.20	1.25	0.045	0.047	0.049	
Е	0.75	0.80	0.85	0.03	0.032	0.034	
е	0.40 BSC			0.016 BSC			
ΗE	1.15	1.20	1.25	0.045	0.047	0.049	
L	0.15	0.20	0.25	0.0059	0.0079	0.0098	



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and

Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and in are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product customer paper and the SCILLC product so ray such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death as secure to a participate during with such with such unintended or unauthorized use payenses. associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative